ELECTRON DRIFT, DIFFUSION, AND EFFECTIVE IONIZATION COEFFICIENTS IN SF₆-CHF₃ AND SF₆-CF₄ MIXTURES FROM BOLTZMANN ANALYSIS

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ABSTRACT

The electron drift velocity, electron energy distribution function and density-normalized effective ionization coefficient are calculated for SF₆-CHF₃ and SF₆-CF₄ mixtures. Two-term, spherical harmonic expansion approximation is utilized to calculate the swarm parameters in steady-state Townsend form Boltzmann analysis. Results show that the drift velocity V_p varies feebly with SF_6 content. On the other hand, a strong dependence is observed in densitynormalized effective ionization coefficient with SF₆ content, the gas mixture becomes more electronegative as the share of SF₆ in gas mixtures increases. The calculated value E/N_{cr} of SF₆-CHF₃ and SF₆-CF₄ mixtures is lower than measured value of SF₆-N₂. The calculated density-normalized effective ionization coefficients obtained in the paper are compared with measured data from pulsed Townsend experiments. The predicted results in the numerical simulation are in agreement with the experimental results.

1. INTRODUCTION

Due to its outstanding electrical, physical and excellent thermal characteristics, Sulfur Hexafluoride has been widely used in the electrical industry. Whereas a major concern have emerged that SF_6 is supposed to be a remarkable greenhouse gas, with a global warming potential 24 000 times greater than that of CO_2 for a 100 year period. In order to decrease the greenhouse impact, SF_6 involved mixtures with less harmful fluorocarbon gases have been

therefore investigated as alternatives to be used in electric power engineering.

 SF_6 -CHF₃ and SF_6 -CF₄ have been identified as effective alternatives to pure SF_6 . Urquijo has measured of electron drift, diffusion and effective ionization coefficients in SF_6 -CHF₃ and SF_6 -CF₄ gas mixtures using pulsed Townsend method[1]. The theoretical calculation based on the numerical solutions of Boltzmann equation have been widely investigated in relevant studies for SF_6 involved mixtures[2-4], whereas numerical analysis regarding SF_6 -CHF₃ and SF_6 -CF₄ are rare.

In this paper, we calculate the electron drift velocity, and density-normalized effective ionization coefficient at various SF₆ content by solving Boltzmann equation with two-term expansion for a steady Townsend discharge. The critical reduced field E/N_{cr} is then determined at which ionization exactly balances attachment. In addition, reliable data of $(\alpha - \eta)/N$ from pulsed Townsend are plotted for the sake of comparison.

2. RESULTS AND DISCUSSION

2.1 Effective ionization coefficients and electron drift velocity of pure SF_6

In the paper, the results from Boltzmann analysis within two-term approximation and the data from direct experimental measurements of the density-reduced effective ionization coefficient in pure SF₆ are compared in Fig. 1. It can be observed that density normalized coefficient $(\alpha - \eta)/N$ increases with increasing reduced field strength. The numerical results are in agreement with

previously published values. Thus, the possibility of utilizing a two-term Boltzmann code constitutes a great advantage especially when dealing with a large number of computations.



Fig. 1 Density normalized effective ionization coefficient as a function of reduced field strength at different for pure SF_6

2.2 The electron energy distribution functions, EEDF

Fig. 2 excludes the mean electron energy as a function of SF_6 content for SF_6 -CHF₃ and SF_6 -CF₄ mixtures when E/N = 200 Td . It can be observed that mean electron energy of SF_6 -CHF₃ mixtures decreases with increasing SF_6 content. Contrarily, as the share of SF_6 in SF_6 -CF₄ mixtrues increases, the corresponding mean electron energy of SF_6 -CF₄ decreases slightly. Such discrepancies can be attributed to the variation of EEDF.



The addition of SF₆ in SF₆-CHF₃ mixtures decreases the electron energy distribution function at the vicinity of the origin of energy space $\varepsilon = 0$ as shown in Fig. 3, which leads to

the decrease of mean electron energy. With respect to SF_6 - CF_4 mixtures, as the share of SF_6 in gas mixtures increases, electron energy distribution function hardly differs near $\varepsilon = 0$, whereas the electron energy distribution function shifts to the right in the low electron energy region as shown in Fig. 4, which causes the mean electron energy of SF_6 - CF_4 mixtures increases with increasing SF_6 content.



Fig. 3 Electron energy distribution functions of SF₆-CHF₃ mixtures



Fig. 4 Electron energy distuibution functions of SF6-CF4 mixtures

2.3 Drift velocity

Fig. 5 and Fig. 6 describe the calculated electron drift velocity as a function of reduced field strength for SF₆-CHF₃ and SF₆-CF₄ mixtures. As it can seen from the figures, drift velocity V_D increases with increasing reduced field strength and it varies weakly when the share of SF₆ in

SF₆-CHF₃ and SF₆-CF₄ mixtures varies form 1% to 100%, especially in the relatively high reduced field region. At a fixed reduced field strength, the drift velocity decreases gradually with increasing SF₆ content for SF₆-CHF₃ and SF₆-CF₄ mixtures. The reasons for the changes in drift velocity V_p are twofold. Primarily, the effective collision frequencies for momentum transfer in SF₆ and CHF_3/CF_4 weigh differently as the share of SF_6 in gas mixtures varies. In addition, the most important changes arise from the modifications on the EEDF as the SF₆ content increases. It can be also noted the interaction of electrons within the gas mixtures is strongly dominated by CHF₃ and CF₄, especially for CHF₃ in SF₆-CHF₃ mixtures, in which the electron drift velocity V_p decreases very feebly with SF₆ content even in the low reduced field strength E/N region due to the fact that CHF₃ is a highly polar molecule^[5].



Fig. 5 Electron drift velocity as a function of reduced field strength for SF₆-CHF₃ mixtures



Fig. 6 Electron drift velocity as a function of reduced field strength for SF₆-CF₄ mixtures

3.4 Density-normalized effective ionization coefficient and critical field strength.

The density-normalized effective ionization coefficients $(\alpha - \eta) / N$ calculated in the paper for and SF₆-CHF₃ and SF₆-CF₄ gas mixtures with 1%, 15%, 25%, 50%, 75% and 100% as a function of reduced field strength are displayed in Fig. 7 and Fig. 8. It indicates that densitynormalized effective ionization coefficient $(\alpha - \eta) / N$ increases with increasing reduced field E/N. For a given value, it decreases as the share of CHF₃/CF₄ content in gas mixtures decreases. This is a consequence of the increasingly electronegative character of the SF₆-CHF₃ and SF₆-CF₄ gas mixtures. For the sake of comparison with published, reliable data are displayed as well.



Fig. 7 The density-normalized ionization coefficient for SF₆-CHF₃ mixtures



In what concerns now the E/N_{cr} , the critical values at which ionization exactly balances attachment when $(\alpha - \eta)/N = 0$, as a function of

 SF_6 content in SF_6 -CHF₃ and SF_6 -CF₄ gas mixtures are plotted in Fig. 9, together with the Urquijo's experimental data and those for SF_6-N_2 mixture for the sake of comparison, since the SF₆-N₂ have been widely studied in relevant studies. It can be seen the critical reduced strength E/N_{cr} increases with increasing SF₆ content, yet the value of E/N_{cr} varies weakly between SF₆-CHF₃ and SF₆-CF₄ gas mixtures as SF₆ content increases. Moreover the agreement between theory and experiment is acceptable in SF₆-CHF₃ and fair in SF₆-CF₄ although some discrepancies are observed as the share of SF₆ in gas mixtures increases. The overall calculated values E/N_{cr} in SF₆-CHF₃ are higher than the measured data while the critical values are lower than the measured data in SF₆-CF₄ mixtures with SF₆ content variation. Now that the E/N_{cr} values in SF₆-N₂ are consistently higher than those in SF₆-CHF₃ and SF₆-CF₄ gas mixtures as indicated by [9], the critical values are by far larger in SF_6 - N_2 than in other SF_6 involved gas mixtures, due to the relatively low ionization rate coefficients in N₂ and the influence of N₂ as a good electron scattered that performs in the overall attachment process.



3. CONCLUSION

In this paper, density normalized effective ionization coefficients, electron energy distribution function and electron drift velocity for are all calculated using Boltzmann equation along with two-term approximation for SF₆-CHF₃ and SF₆-CF₄ mixtures. The critical electric field strength E/N_{cr} , at which the ionization and attachment rate are exactly balanced, is determined for SF₆-CHF₃ and SF₆-CF₄ mixtures as a function of SF_6 content. By comparing with the previous published values, two-term expansion is confirmed to be a valid approach.

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